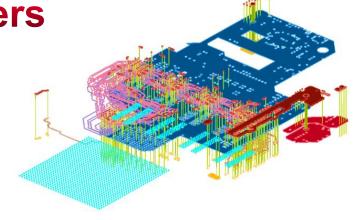
Power Integrity Boot Camp for Designers

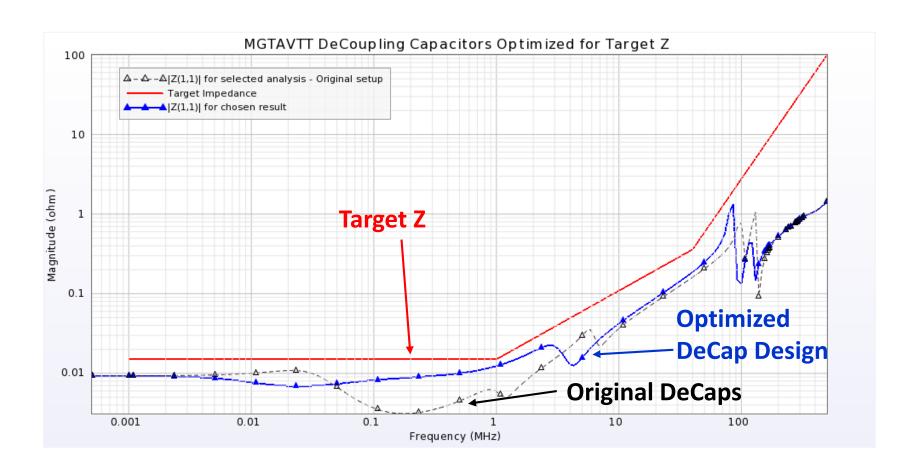
Section 4 Decoupling Capacitor Optimization and the Power Integrity Ecosystem

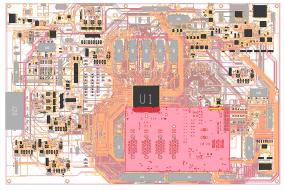






PCB Decoupling Capacitor Optimization





Decoupling Capacitors

Yes C190 330 uF Yes C215 330 uF Yes C216 330 uF Yes C218 330 uF Yes C218 330 uF Yes C303 220 nF Yes C305 220 nF Yes C750 220 nF Yes C753 220 nF Yes C757 220 nF No C217 100 uF No C225 100 uF No C315 4.7 uF No C316 4.7 uF No C778 4.7 uF No C780 4.7 uF			
Yes C216 330 uF Yes C218 330 uF Yes C303 220 nF Yes C305 220 nF Yes C750 220 nF Yes C753 220 nF Yes C757 220 nF No C217 100 uF No C225 100 uF No C315 4.7 uF No C778 4.7 uF No C779 4.7 uF	Yes	C190	330 uF
Yes C218 330 uF Yes C303 220 nF Yes C305 220 nF Yes C750 220 nF Yes C753 220 nF Yes C757 220 nF No C217 100 uF No C225 100 uF No C315 4.7 uF No C778 4.7 uF No C779 4.7 uF	Yes	C215	330 uF
Yes C303 220 nF Yes C305 220 nF Yes C750 220 nF Yes C753 220 nF Yes C757 220 nF No C217 100 uF No C225 100 uF No C315 4.7 uF No C778 4.7 uF No C779 4.7 uF	Yes	C216	330 uF
Yes C305 220 nF Yes C750 220 nF Yes C753 220 nF Yes C757 220 nF No C217 100 uF No C225 100 uF No C315 4.7 uF No C778 4.7 uF No C779 4.7 uF	Yes	C218	330 uF
Yes C750 220 nF Yes C753 220 nF Yes C757 220 nF No C217 100 uF No C225 100 uF No C315 4.7 uF No C778 4.7 uF No C779 4.7 uF	Yes	C303	220 nF
Yes C753 220 nF Yes C757 220 nF No C217 100 uF No C225 100 uF No C315 4.7 uF No C316 4.7 uF No C778 4.7 uF No C779 4.7 uF	Yes	C305	220 nF
Yes C757 220 nF No C217 100 uF No C225 100 uF No C315 4.7 uF No C316 4.7 uF No C778 4.7 uF No C779 4.7 uF	Yes	C750	220 nF
No C217 100 uF No C225 100 uF No C315 4.7 uF No C316 4.7 uF No C778 4.7 uF No C779 4.7 uF	Yes	C753	220 nF
No C225 100 uF No C315 4.7 uF No C316 4.7 uF No C778 4.7 uF No C779 4.7 uF	Yes	C757	220 nF
No C225 100 uF No C315 4.7 uF No C316 4.7 uF No C778 4.7 uF No C779 4.7 uF			
No C315 4.7 uF No C316 4.7 uF No C778 4.7 uF No C779 4.7 uF	No	C217	100 uF
No C316 4.7 uF No C778 4.7 uF No C779 4.7 uF	No	C225	100 uF
No C778 4.7 uF No C779 4.7 uF	No	C315	4.7 uF
No C779 4.7 uF	No	C316	4.7 uF
	No	C778	4.7 uF
No C780 4.7 uF	No	C779	4.7 uF
	No	C780	4.7 uF

40% Fewer Components

Fewer solder joints higher reliability

Design Methodology for DeCap Optimization

3 STEP PROCESS

1. Calculate 1st order approximations

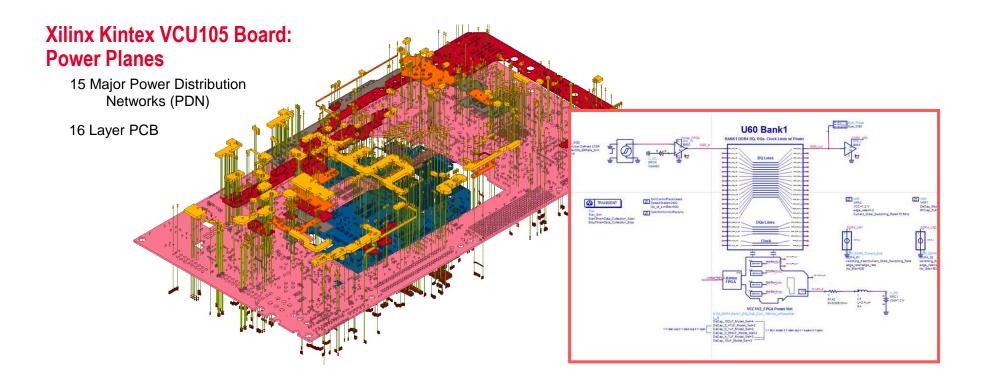
$$C_{bulk} = \frac{L_{supply}}{Z_{Target}^2}$$

$$C_{bulk} = rac{L_{supply}}{Z_{Target}^2}$$
 $C_{decap} = rac{ESL_{Cbulk}}{Z_{Target}^2}$

$$\operatorname{Max} L_{PDN} = C_{pkg} * Z_{Target}^{2}$$

- 2. Use Target Z to optimize the decoupling capacitor selection using high fidelity EM models (ADS PIPro)
- 3. Validate with full Power Integrity Eco-System simulation in ADS

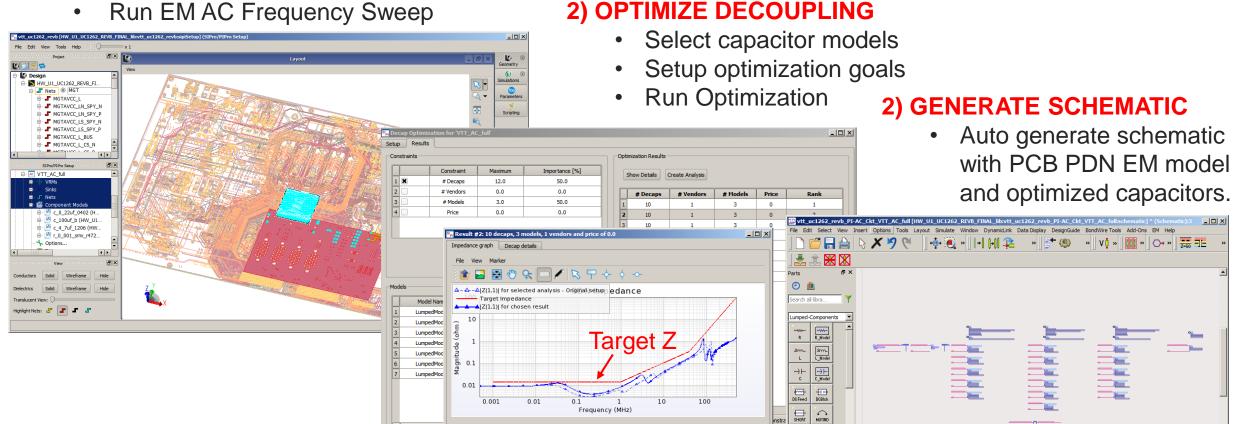
Modern Applications with Multiple PDNs



ADS PIPro EM Simulation of the PCB PDN

IMPORT THE PCB

- Select VRM, Sink, Nets, Components
- Run EM AC Frequency Sweep



GD. ·(;;)· Parts Layers Select: Click and drag to select



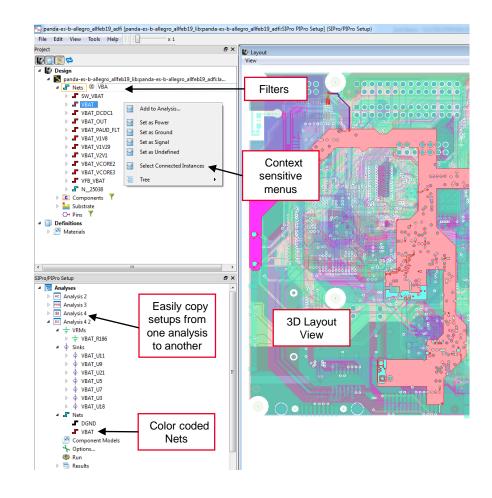


ads_device:drawing 36.625, 34.875

PIPro: PI-specific use-model and flow

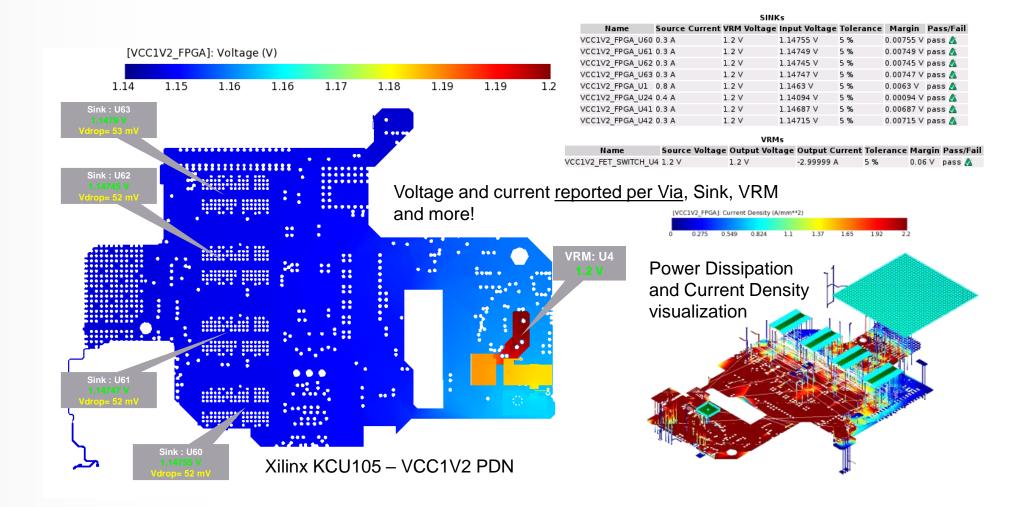
Designed for Usability

- Filter by Net
- Filter by Component
- Right-click to add-to-analysis
- Drag & Drop
- Hierarchical search for complex selections
- Context sensitive menus e.g. 'Select instances connected to ONLY the selected nets'





PIPro – DC IR Drop





How to Interpret the Power Graph?

Voltage relative to ideal Power graph ground reference* Voltage at VRM P DC Results Overview - VDD_GND_DC **VRM** Sink File Options.. Thermal Components Lavers Pins Vias VDD_U1 ± 3 % 1.199 V ΔV 1.0 mV VDD U5 1.199 V Vnom = 1.20 V VDD J1 1.80 A 1.20 V VDD 1.196 V Vnom = 1.20 V 1.80 A 1.00 A **VRM** 1 % 1.199 V ΔVp 3.6 mV ΔVg 2.1 mV 1.199 V Total current at VRM Total current at the sink 1.199 V Voltage relative to ideal Voltage relative to Sink ground reference* sink reference* 1.200 V 1.199 V VDD U5 1.196 V 1.200 V 1.196 V 1.194 V 1.00 A ΔV 5.7 mV ΔVp 3.6 mV ΔVq 2.1 mV IR drop in the power plane



*Try turning ideal ground on and off and see how power graph changes

IR drop in the ground plane

DC Electro - Thermal Design Challenge

WATCH OUT FOR HIGH CURRENT DENSITIES IN THE GROUND RETURN PATH

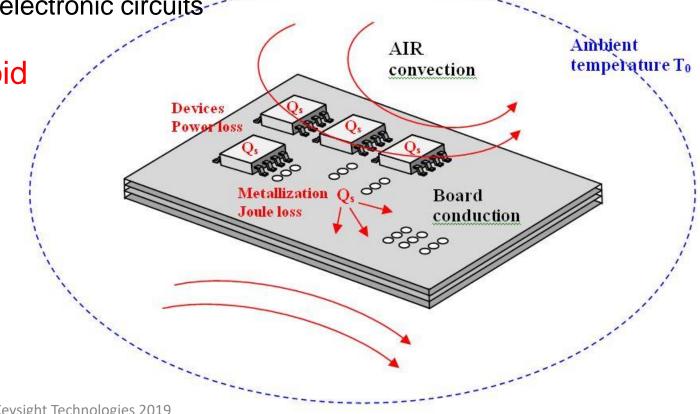
- Electronic devices produce HEAT
- Joule losses in metallization produce **HEAT**

Heat is transferred to the ambient (conduction, convection, radiation)

Heat causes a **Temperature rise** in the electronic circuits-

Thermal validation is needed to avoid

- Component overheating
- Thermal stress
- Electronic malfunctioning





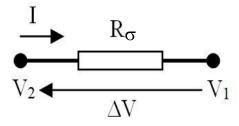
#1 – Thermal Run Away

WATCH OUT FOR CURRENT CONSTRICTION POINTS

Coupled Electro-Thermal Equations

Electric resistance R_{σ} [V/A]

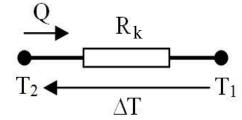
$$V_2 - V_1 = R_{\sigma} \cdot I$$



...Where electric resistance R_{σ} changes with temperature T

Thermal resistance R_k [K/W]

$$T_2 - T_1 = R_k \cdot Q$$

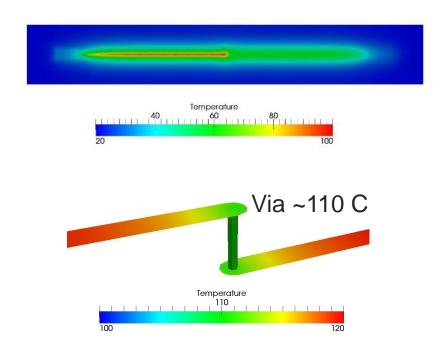


...Where the injected heat flux Q changes with voltage V

Thermal is Non-Intuitive: IPC Got it Wrong

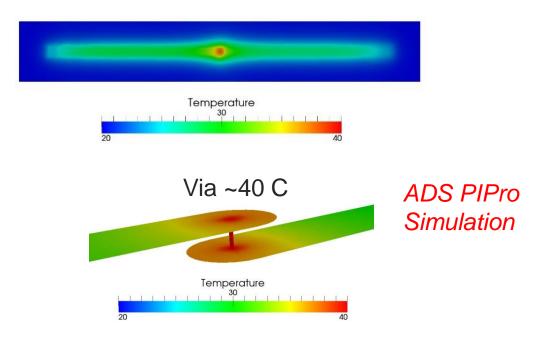
HIGH CURRENT DENSITY IN A SINGLE POINT GROUND RETURN CONNECTION

27 mil trace ≅ Via Cross Section



Equivalent cross section via has more conductive cooling than the trace.

200 mil trace >> Via Cross Section



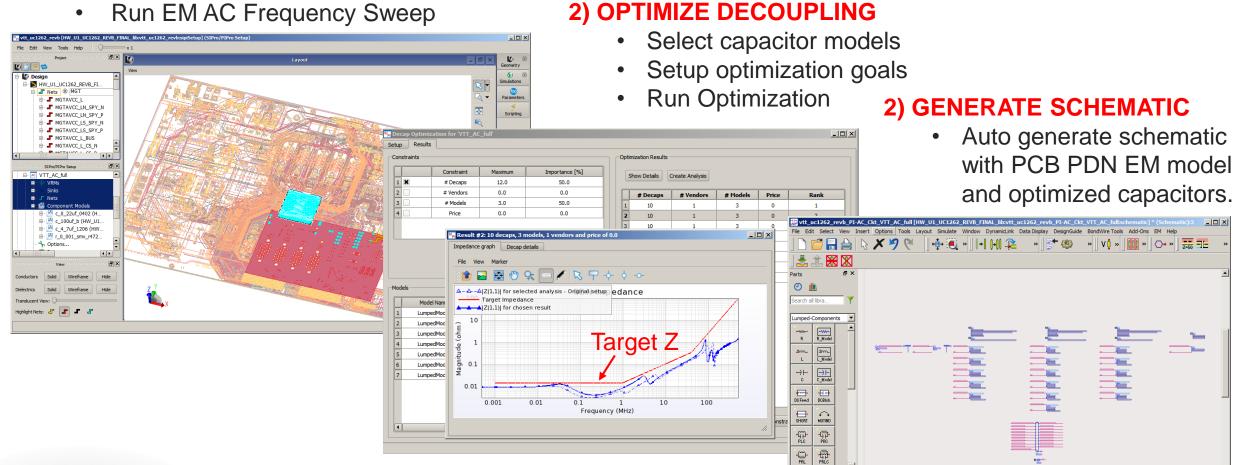
Wide trace provides conductive cooling for the via.



ADS PIPro EM Simulation of the PCB PDN

IMPORT THE PCB

- Select VRM, Sink, Nets, Components
- Run EM AC Frequency Sweep

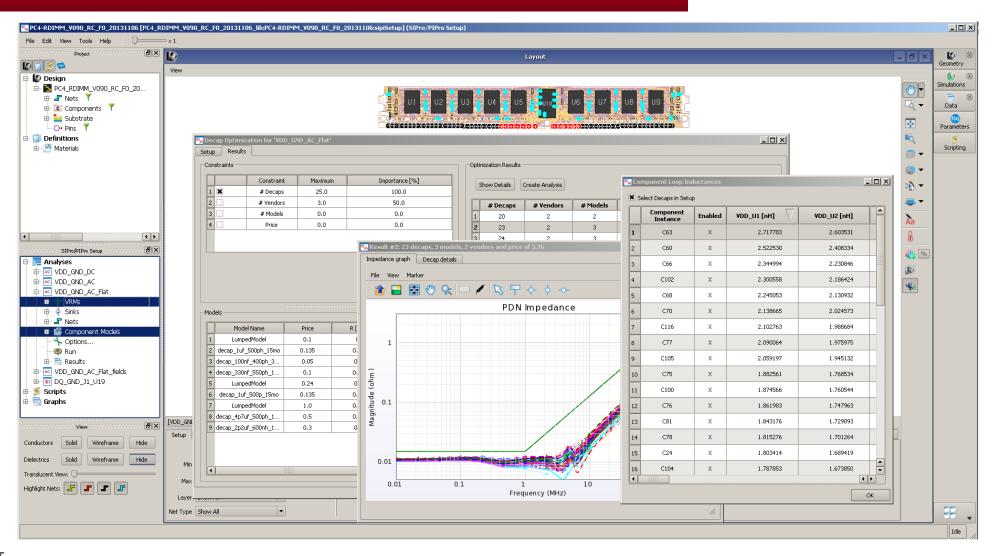


Select: Click and drag to select

ads device:drawing 36.625, 34.875

DDR4 DIMM Example – Ships with ADS

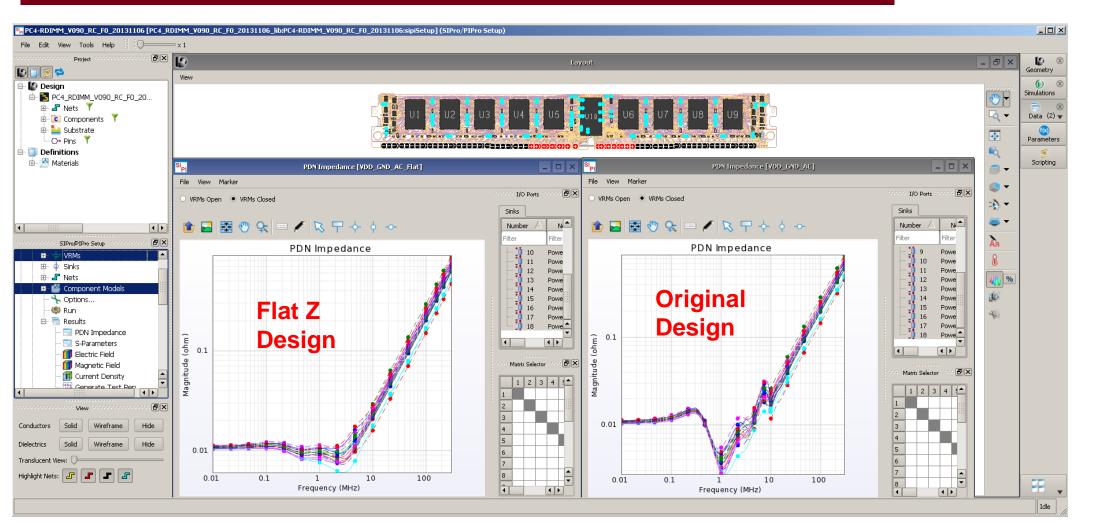
DECOUPLING CAPACITOR OPTIMIZATION FOR FLAT Z



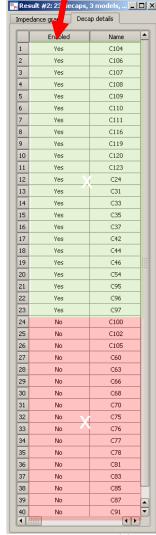


PCB Decoupling Capacitor Optimization

FLAT IMPEDANCE VS FREQUENCY FOR BEST PERFORMANCE



Flat Z with 40% fewer capacitors





Voltage Regulator State Spaced Averaged Models

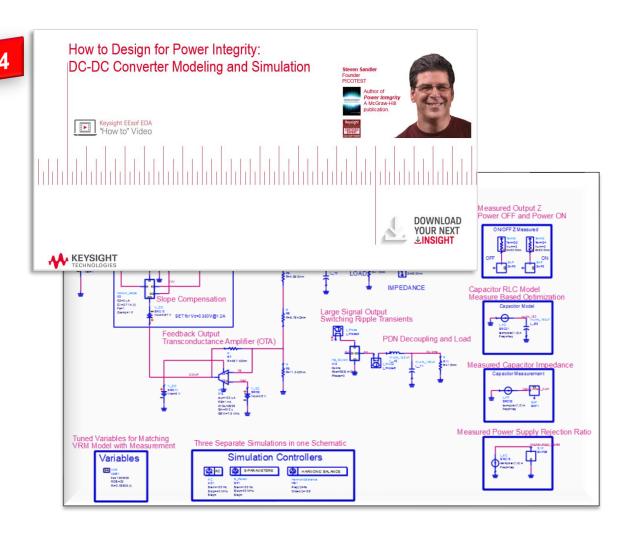
Measurement Based VRM Modeling



Steve Sandler - PICOTEST









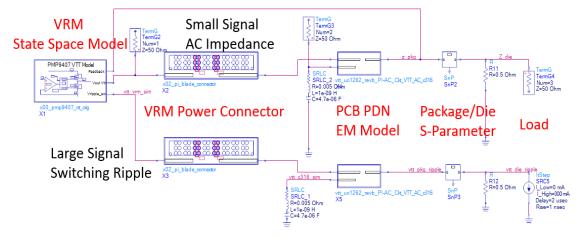


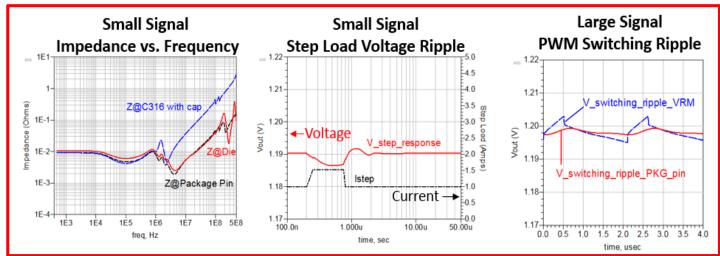
Modeling the Power Integrity Ecosystem

VRM + PDN + Load = PI Ecosystem

Three Separate Simulations in one Schematic



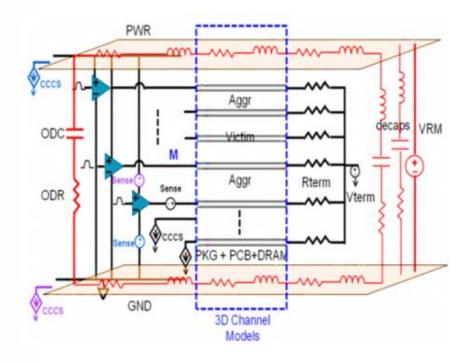








SI and PI Co-EM Simulation



Power and Signal Nets in the same EM simulation



Vendor Specific IBIS Models to Improve Accuracy

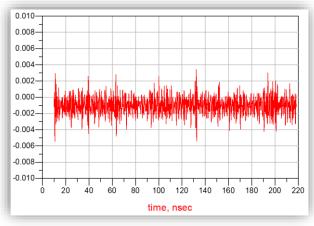
 Xilinx Kintex FPGA and Micron DDR4 IBIS models **U60** U60 DDR4 DQ, DQs, Clock Lines w/ Power DQ0_in DQ2_out DQ Lines DQ6 out DQ7 in DQ7 out DQ8 out DQ9 in DQ9 out DQ10 out DQ11 out SYM_DDR4_Micron_RX_BUS VCC1V2 FPGA Power Net SYM_DDR4_U60_DQ_DQs_CLK_wPowerNet_LowESR Kintex IBIS Micron IBIS

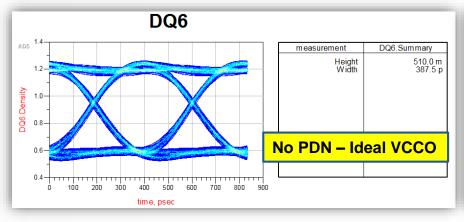


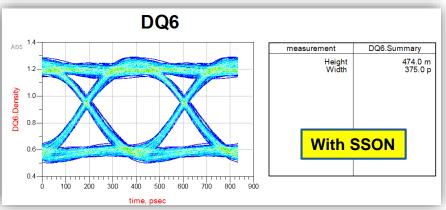
Simultaneous Switching Noise (SSN)

- Shows SSN noise voltage at VCCO pin, which is similar to the measured data
 - Both eye width and height are reduced by SSO noise, as expected.
 - 387.5p → 375p, **510mV** → **474mV** respectively

VCCO Pin Noise Voltage By SSON



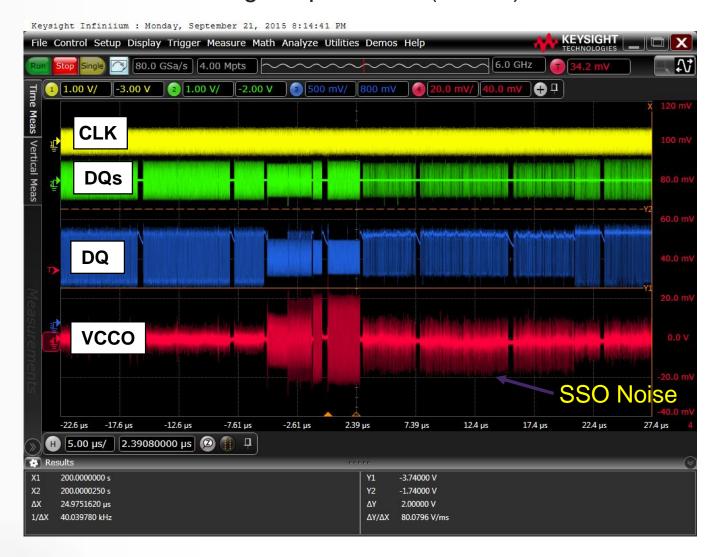


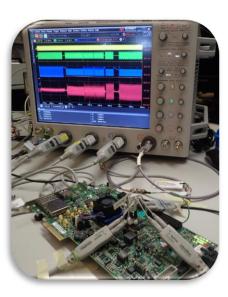




SSO Noise Measured Example

Simultaneous Switching Output Noise (SSON)







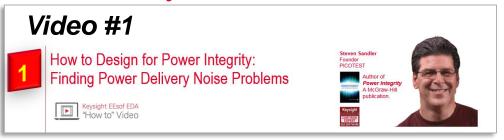
Summary

- How parallel resonances lead to significant voltage ringing on the power rail
- How to calculate decoupling C for a flat target Z
- The impact of Capacitor PCB mounting parasitics
- ADS with PIPro DeCap Optimization for reduced part count and full PI Ecosystem simulation

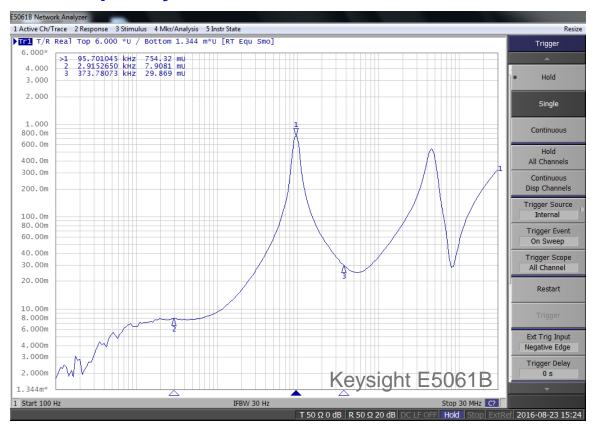




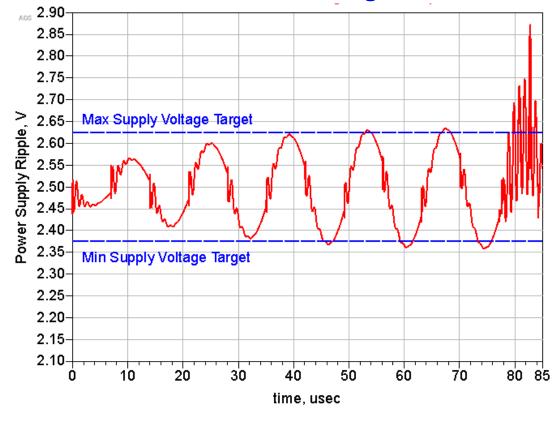
PDN Disasters Do Exist – Always Look at the PDN Impedance!



Frequency Domain Shows Resonances



Time Domain Excitation – Rogue Wave Failure







Big Screen Simulation and Measurement Demo

- E5061B Network Analyzer Impedance Parallel Capacitors
- ADS PIPro Demo of DeCap Optimization





Hands-On Lab: 190219_ADS_PI_Lab4_DeCap_Optimize_v2_wrk.7zads

Basics – Instructor Led Demo

Flat Z Capacitor Selection

Explore –

Parallel Capacitor SPICE vs. EM Models

Advanced -

PIPro Decoupling Capacitor Optimization



